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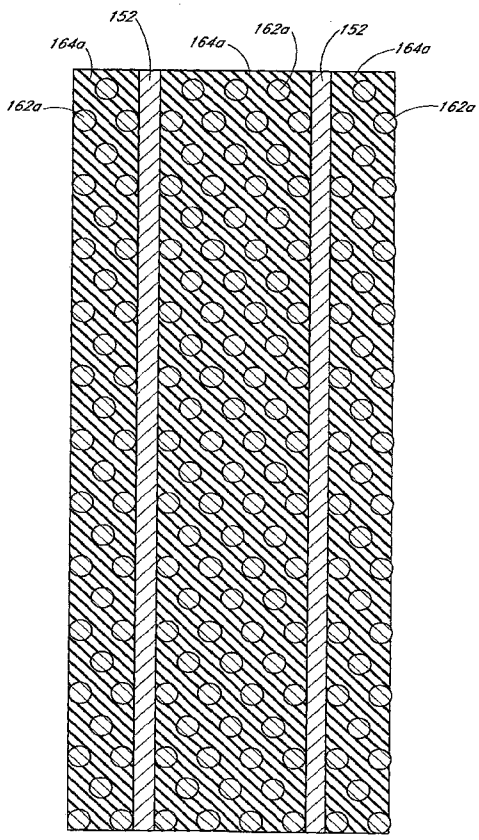
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(57) Abstract: A pattern having exceptionally small features is formed on a partially fabricated integrated circuit (102) during integrated circuit fabrication. The pattern comprises features (162), (164) formed by self-organizing material, such as diblock copolymers. The organization of the copolymers is directed by spacers (152) which have been formed by a pitch multiplication process in which the spacers (152) are formed at the sides of sacrificial mandrels (142), which are later removed to leave the spaced-apart, free-standing spacers (152). Diblock copolymers, composed of two immiscible block species, are deposited over and in the space between the spacers (152). The copolymers are made to self-organize, with each block species aggregating with other block species of the same type.

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